



PHPT61003PY

100 V, 3A PNP high power bipolar transistor

13 January 2014

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61003NY

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Loadswitch
- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------|---|--|-----|-----|------|------------|
| V_{CEO} | collector-emitter voltage | open base | - | - | -100 | V |
| I_C | collector current | | - | - | -3 | A |
| I_{CM} | peak collector current | $t_p \leq 1$ ms; single pulse | - | - | -8 | A |
| R_{CEsat} | collector-emitter saturation resistance | $I_C = -2$ A; $I_B = -200$ mA; pulsed; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_{amb} = 25$ °C | - | 110 | 180 | m Ω |

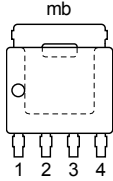
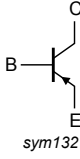


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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--|---|
| 1 | E | emitter |  <p>LFPAK56; Power-SO8 (SOT669)</p> |  |
| 2 | E | emitter | | |
| 3 | E | emitter | | |
| 4 | B | base | | |
| mb | C | collector | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|--------------------|--|---------|
| | Name | Description | Version |
| PHPT61003PY | LFPAK56; Power-SO8 | Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads | SOT669 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PHPT61003PY | 1003PAB |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V _{CBO} | collector-base voltage | open emitter | | - | -100 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | -100 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | -8 | V |
| I _C | collector current | | | - | -3 | A |
| I _{CM} | peak collector current | t _p ≤ 1 ms; single pulse | | - | -8 | A |
| I _B | base current | | | - | -0.5 | A |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 1.25 | W |
| | | | [2] | - | 3 | W |
| | | | [3] | - | 5 | W |
| | | | [4] | - | 25 | W |
| T _j | junction temperature | | | - | 175 | °C |
| T _{amb} | ambient temperature | | | -55 | 175 | °C |
| T _{stg} | storage temperature | | | -65 | 175 | °C |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.
- [4] Power dissipation from junction to mounting base.

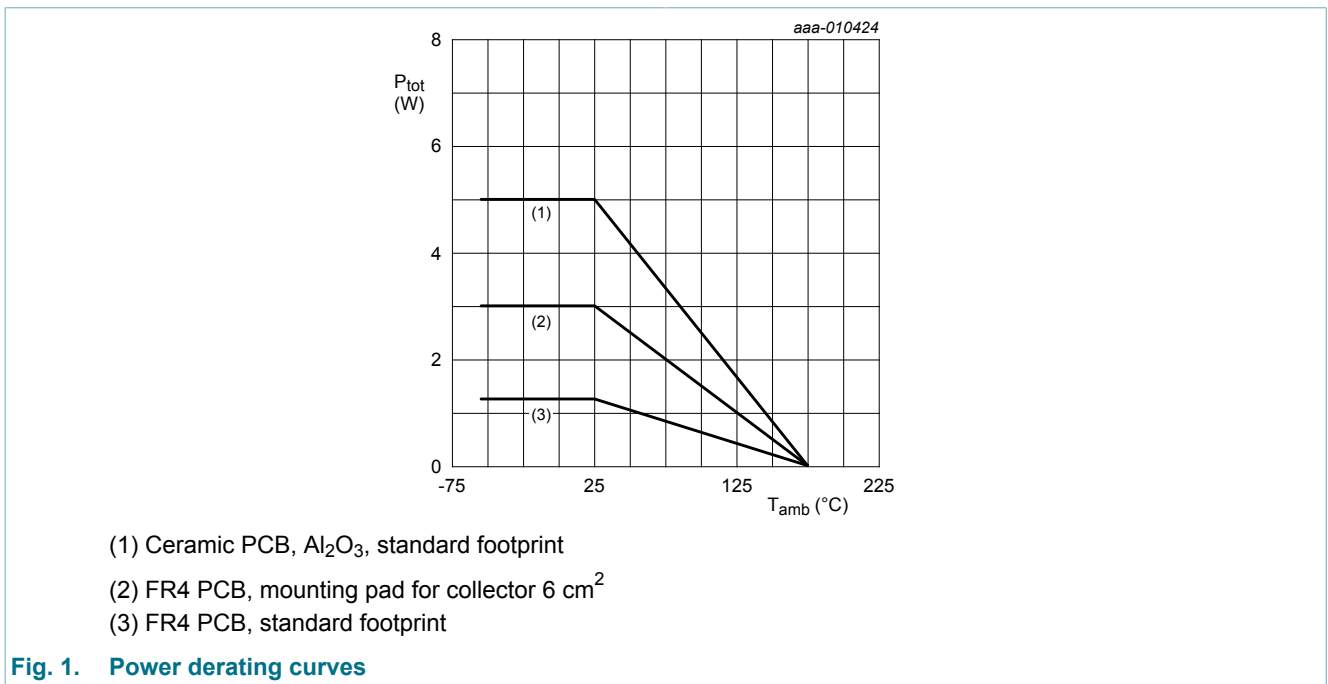


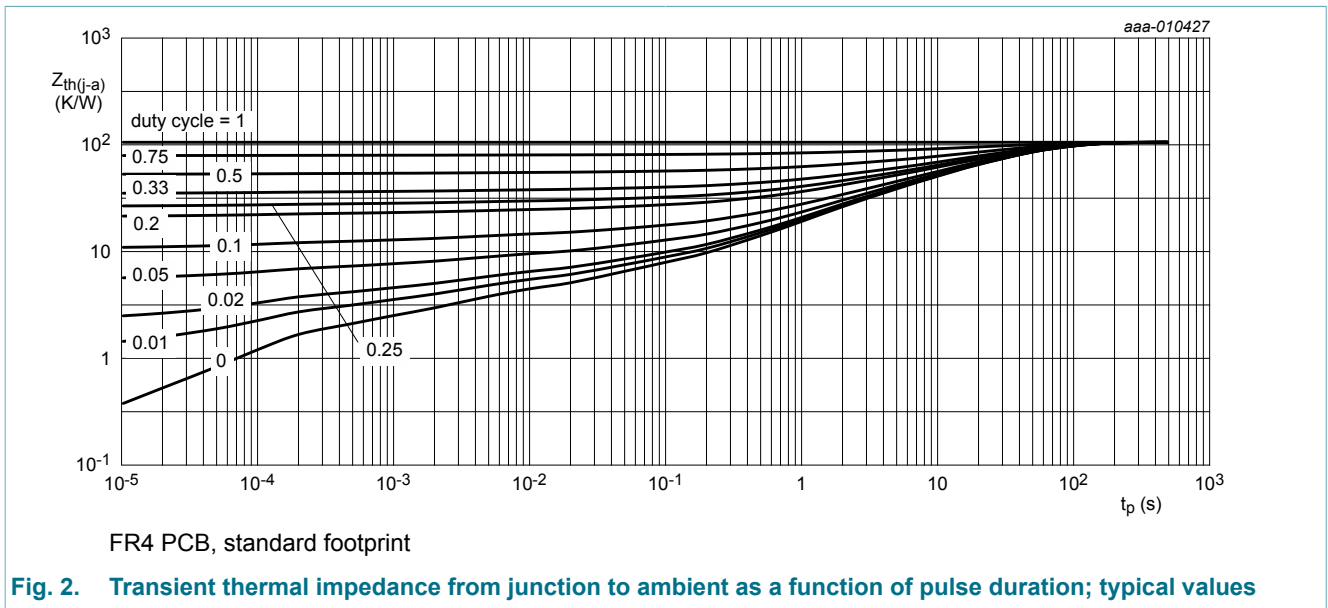
Fig. 1. Power derating curves

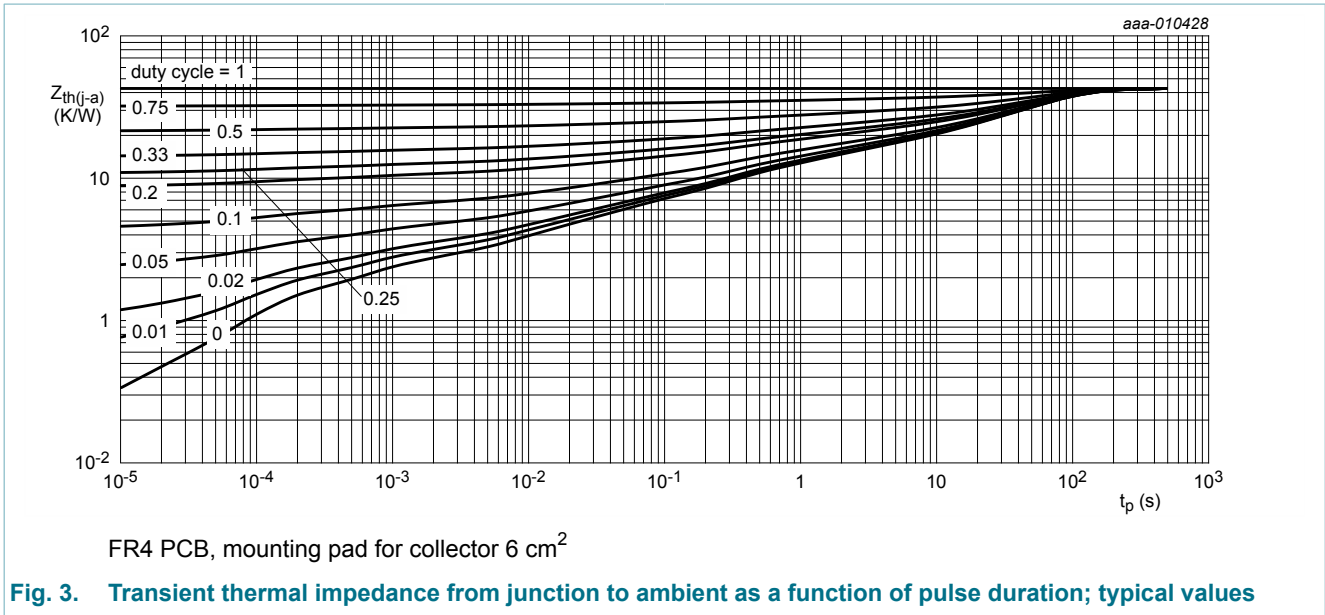
9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | [1] | - | - | 115 | K/W |
| | | | [2] | - | - | 50 | K/W |
| | | | [3] | - | - | 30 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 6 | K/W |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.



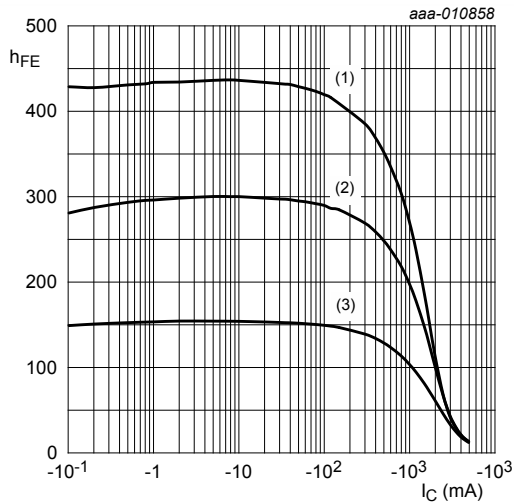


10. Characteristics

Table 7. Characteristics

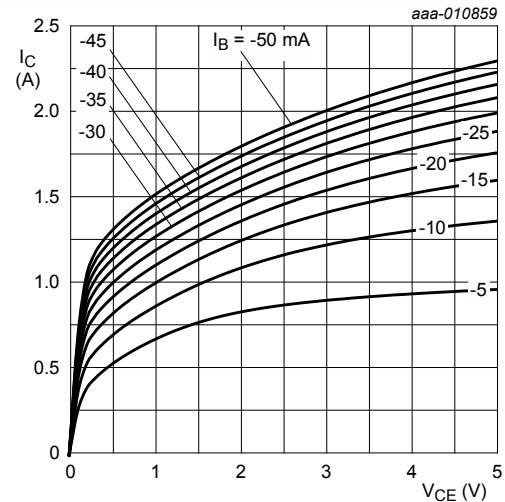
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------|---|--|--|-------|------|------|
| I _{CBO} | collector-base cut-off current | V _{CB} = -80 V; I _E = 0 A; T _{amb} = 25 °C | - | - | -100 | nA |
| | | V _{CB} = -80 V; I _E = 0 A; T _j = 150 °C | - | - | -50 | μA |
| I _{CES} | collector-emitter cut-off current | V _{CE} = -80 V; V _{BE} = 0 V; T _{amb} = 25 °C | - | - | -100 | nA |
| I _{EBO} | emitter-base cut-off current | V _{EB} = -8 V; I _C = 0 A; T _{amb} = 25 °C | - | - | -100 | nA |
| h _{FE} | DC current gain | V _{CE} = -10 V; I _C = -500 mA; T _{amb} = 25 °C | 150 | 220 | - | |
| | | V _{CE} = -10 V; I _C = -1 A; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed | 80 | 210 | - | |
| | | V _{CE} = -10 V; I _C = -2 A; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed | 20 | 100 | - | |
| | | V _{CE} = -10 V; I _C = -3 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C | 10 | 40 | - | |
| V _{CEsat} | collector-emitter saturation voltage | I _C = -500 mA; I _B = -50 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C | - | -70 | -110 | mV |
| | | I _C = -2 A; I _B = -200 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C | - | -220 | -360 | mV |
| R _{CEsat} | collector-emitter saturation resistance | I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C | - | 110 | 180 | mΩ |
| V _{BEsat} | base-emitter saturation voltage | I _C = -1 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C | - | -0.91 | -1 | V |
| | | I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C | - | -1.02 | -1.2 | V |
| V _{BEon} | base-emitter turn-on voltage | V _{CE} = -2 V; I _C = -100 mA; T _{amb} = 25 °C | - | -0.68 | -0.9 | V |
| t _d | delay time | V _{CC} = -12.5 V; I _C = -1 A; I _{Bon} = -50 mA; I _{Boff} = 50 mA; T _{amb} = 25 °C | - | 20 | - | ns |
| t _r | rise time | | - | 180 | - | ns |
| t _{on} | turn-on time | | - | 200 | - | ns |
| t _s | storage time | | - | 350 | - | ns |
| t _f | fall time | | - | 220 | - | ns |
| t _{off} | turn-off time | | - | 570 | - | ns |
| f _T | transition frequency | | V _{CE} = -10 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C | - | 125 | - |

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------|-----------------------|--|-----|-----|-----|------|
| C_c | collector capacitance | $V_{CB} = -10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A};$ $f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$ | - | 30 | - | pF |



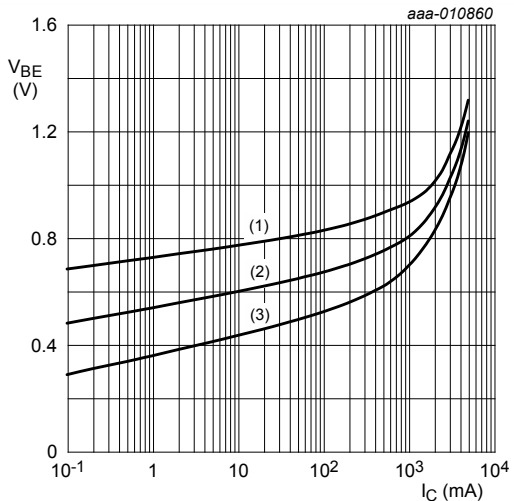
$V_{CE} = -10\text{ V}$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 4. DC current gain as a function of collector current; typical values



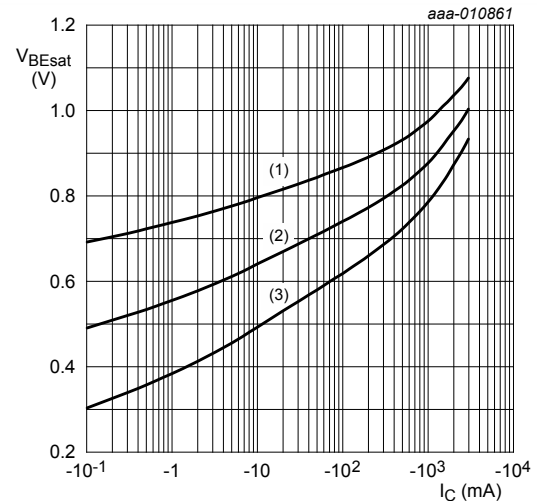
$T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 5. Collector current as a function of collector-emitter voltage; typical values



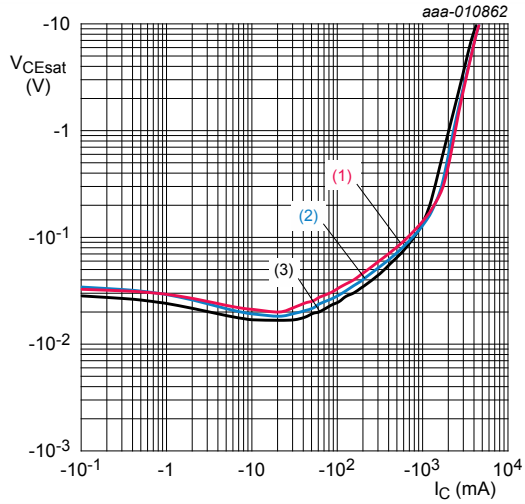
$V_{CE} = -2\text{ V}$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



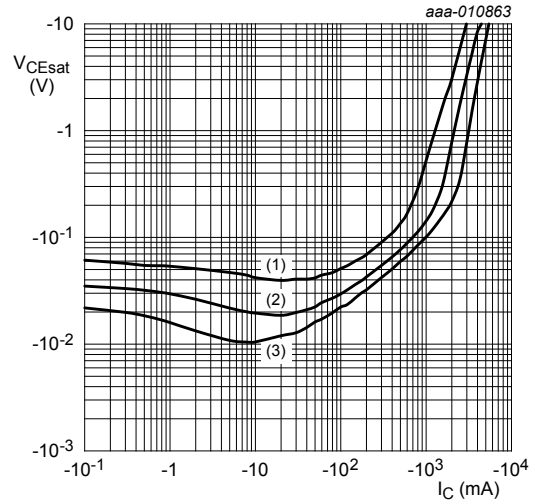
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



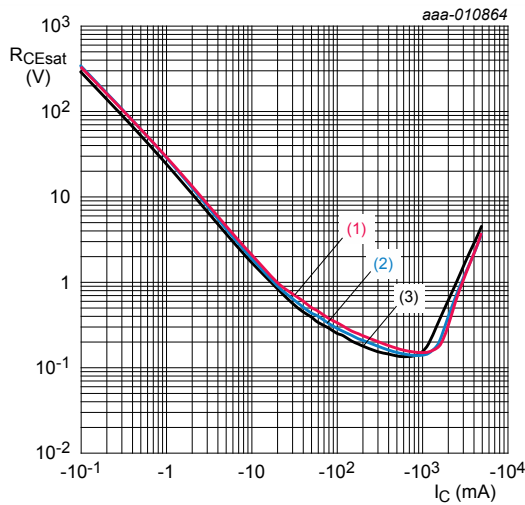
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



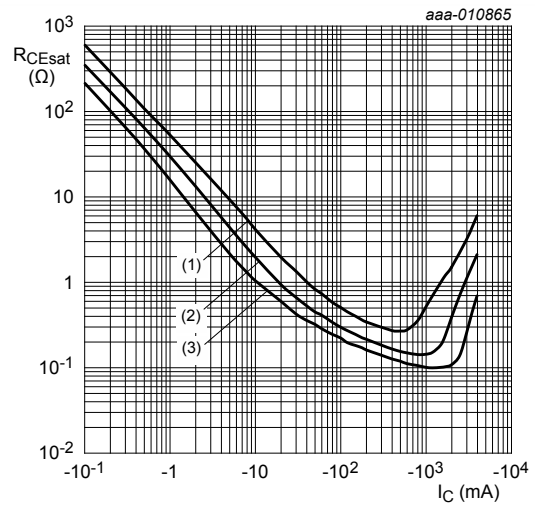
$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 50$
 (2) $I_C/I_B = 20$
 (3) $I_C/I_B = 10$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 50$
 (2) $I_C/I_B = 20$
 (3) $I_C/I_B = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

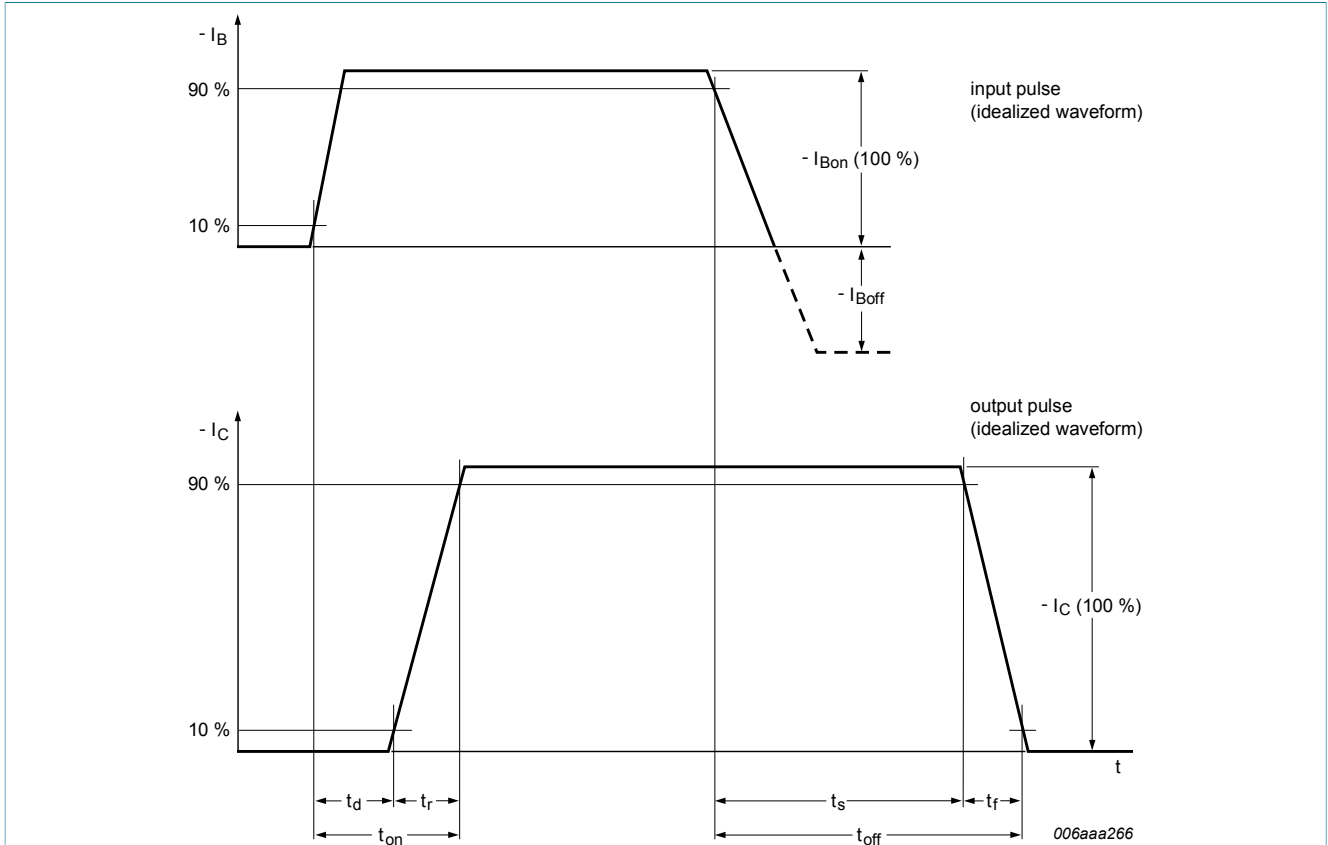


Fig. 12. BISS transistor switching time definition

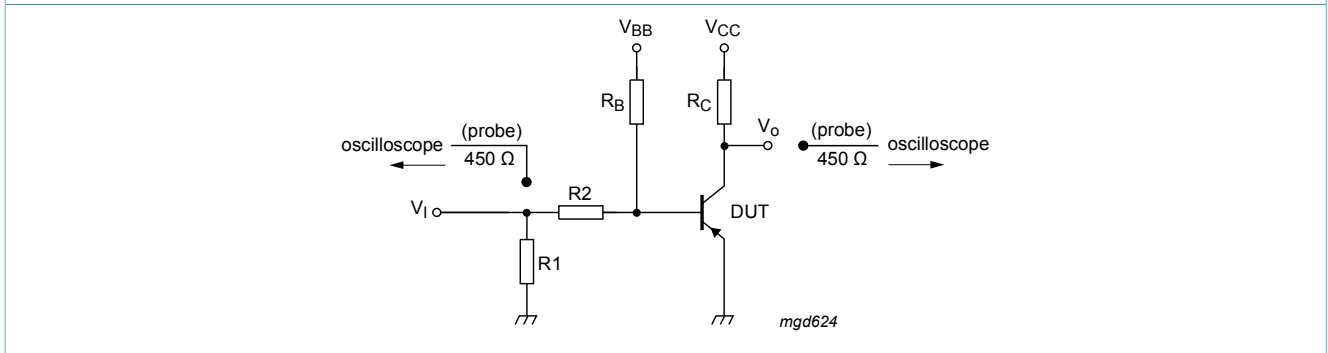


Fig. 13. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

Plastic single-ended surface-mounted package (LFAK56; Power-SO8); 4 leads SOT669



Dimensions (mm are the original dimensions)

| Unit ⁽¹⁾ | A | A ₁ | A ₂ | A ₃ | b | b ₂ | b ₃ | b ₄ | c | c ₂ | D ⁽¹⁾ | D ₁ ⁽¹⁾ | E ⁽¹⁾ | E ₁ ⁽¹⁾ | e | H | L | L ₁ | L ₂ | w | y |
|---------------------|------|----------------|----------------|----------------|------|----------------|----------------|----------------|------|----------------|------------------|-------------------------------|------------------|-------------------------------|------|-----|------|----------------|----------------|------|-----|
| max | 1.20 | 0.15 | 1.10 | | 0.50 | 4.41 | 2.2 | 0.9 | 0.25 | 0.30 | 4.10 | 4.20 | 5.0 | 3.3 | | 6.2 | 0.85 | 1.3 | 1.3 | | |
| nom | | | | 0.25 | | | | | | | | | | | 1.27 | | | | | 0.25 | 0.1 |
| min | 1.01 | 0.00 | 0.95 | | 0.35 | 3.62 | 2.0 | 0.7 | 0.19 | 0.24 | 3.80 | | 4.8 | 3.1 | | 5.8 | 0.40 | 0.8 | 0.8 | | |

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

sot669_po

| Outline version | References | | | | European projection | Issue date |
|-----------------|------------|--------|-------|--|---------------------|------------------------|
| | IEC | JEDEC | JEITA | | | |
| SOT669 | | MO-235 | | | | -11-03-25- 13-02-27 |

Fig. 14. Package outline LFAK56; Power-SO8 (SOT669)

13. Soldering

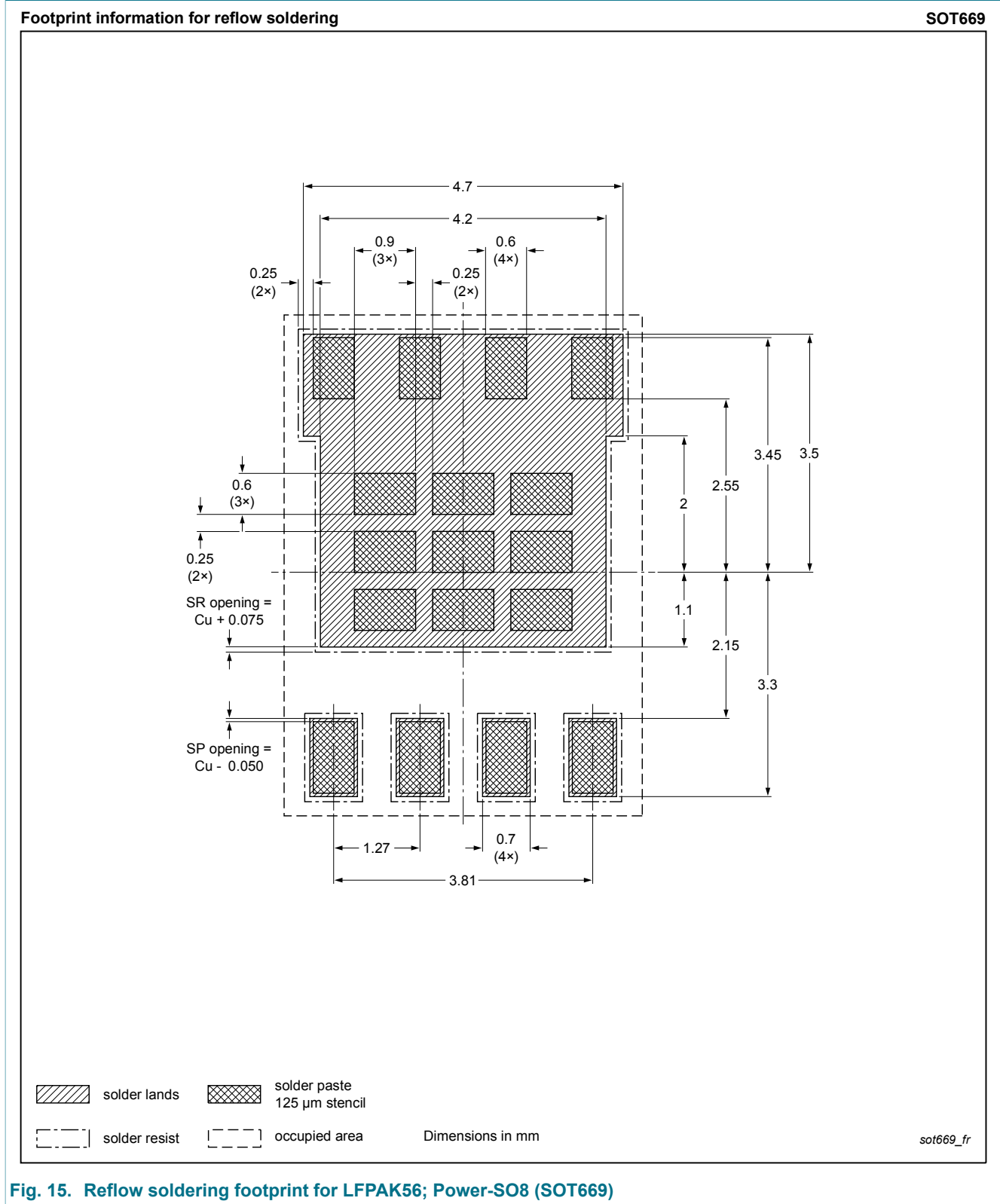


Fig. 15. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| PHPT61003PY v.1 | 20140113 | Product data sheet | - | - |

15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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